



EXPRESS MAIL MAILING LABEL NO. EV 289511710 US

PATENT

Atty. Docket No. ASC-043

(366/29)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

APPLICANTS: Fitzgerald *et al.* CONFIRMATION NO.: 2548  
SERIAL NUMBER: 09/884,517 ART UNIT: 2822  
FILING DATE: June 19, 2001 EXAMINER: K. Duong  
TITLE: CMOS Inverter and Integrated Circuits Utilizing Strained Silicon  
Surface Channel MOSFETs

#18/Cumdt a  
a fee  
4/14/03

Commissioner for Patents  
Washington, D.C. 20231

AMENDMENT AND RESPONSE

This paper is submitted in response to the pending Office Action, Paper No. 13 ("the Office Action"), mailed from the U.S. Patent and Trademark Office on November 29, 2002. Applicants also submit herewith a petition for a one-month extension of time up to and including March 31, 2003 (March 29, 2003 falls on a Saturday), and a check for the appropriate fee. Applicants believe that no additional fee is due for this Amendment and Response to be entered and considered. However, please consider this a conditional petition for the proper extension, if one is required, and a conditional authorization to charge any related extension fees or other fees necessary for entry of this paper to Deposit Account No. 20-0531.

Prior to further examination, please enter the following amendments, without prejudice, and consider the following remarks.

In the Claims

Please cancel claims 2, 13, 14, and 16, and amend claims 1 and 15 to read as follows:

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1. A CMOS inverter comprising:  
a heterostructure including a Si substrate, a relaxed  $\text{Si}_{1-x}\text{Ge}_x$  layer on said Si substrate, and a strained surface layer on said relaxed  $\text{Si}_{1-x}\text{Ge}_x$  layer, the heterostructure further including a planarized surface positioned between the strained surface layer and the Si substrate; and

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